



CRG40T120CK3LDQ

General Description:

Using owner proprietary trench design and advanced Field Stop (FS) technology, offering superior conduction and switching performances. RoHS Compliant.

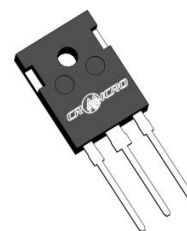
V_{CES}	1200	V
I_C	40	A
P_{tot} ($T_C=25^{\circ}C$)	550	W
$V_{CE(sat)}$	1.80	V

Features:

- Qualified to AEC-Q101
- Short Circuit Withstand Time 10 μ s
- FS Trench Technology, Positive temperature coefficient
- Low saturation voltage:

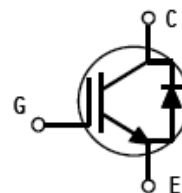
$V_{CE(sat)}$ TYP=1.80V @ $I_C=40A$, $V_{GE}=15V$;

Outline : TO-247

**Applications**

- Electric Automotive Air-Condition Compressor
- PTC heater
- General Inverter

Inner Circuit:

**Package Parameters**

Type	Marking	Package	Packing
CRG40T120CK3LDQ	G40T120CK3LDQ	TO-247	Tube

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	± 20	V
V_{GES}	Gate- Emitter Voltage ($t_p \leq 10\mu\text{s}, D < 0.01$)	± 30	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	80	A
	Collector Current @ $T_C = 100^\circ\text{C}$	40	
I_{CM}^{a1}	Pulsed Collector Current	160	A
I_F	Diode Continuous Forward Current @ $T_C = 25^\circ\text{C}$	80	A
	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	40	
I_{FM}	Diode Maximum Forward Current	160	A
T_{SC}	Short Circuit Withstand Time @ $V_{GE}=15\text{V}, V_{CE}=600\text{V}$	10	μs
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	550	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	275	
T_{vjop}^{a2}	Operating Junction temperature range	$-40 \sim 175$	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	$-55 \sim 150$	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	270	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R\theta_{JC}$	Thermal Resistance, Junction to case for IGBT	--	0.27	$^\circ\text{C}/\text{W}$
$R\theta_{JC}$	Thermal Resistance, Junction to case for Diode	--	1.0	$^\circ\text{C}/\text{W}$
$R\theta_{JA}$	Thermal Resistance, Junction to Ambient	--	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics of the IGBT ($T_C = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ	Max.	
OFF Characteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =250uA	1200	--	--	V
I _{CES}	Collector Cut-off Current	V _{GE} =0V,V _{CE} =1200V	--	--	100	uA
I _{GES(F)}	Gate-Emitter Forward Leakage Current	V _{GE} =+20V	--	--	+250	nA
I _{GES(R)}	Gate-Emitter Reverse Leakage Current	V _{GE} =-20V	--	--	-250	nA
ON Characteristics						
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =40A ,V _{GE} =15V @ T _C = 25 °C	--	1.80	2.4	V
		I _C =40A ,V _{GE} =15V @ T _C =175 °C	--	2.50	--	V

V _{GE(th)}	Gate - Emitter Threshold Voltage	I _C =250uA ,V _{CE} =V _{GE}	4.5	5.8	7.0	V
Pulse width tp≤300μs,δ≤2%						
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} =30V,V _{GE} =0V f=1MHz	--	4067	--	pF
C _{oes}	Output Capacitance		--	167	--	
C _{res}	Reverse Transfer Capacitance		--	90	--	
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{CE} =600V,I _C =40A, R _g =10Ω,V _{GE} =15V, Inductive Load, T _j =25℃,	--	46.5	--	ns
t _r	Rise Time		--	40.4	--	
t _{d(off)}	Turn-Off Delay Time		--	273	--	
t _f	Fall Time		--	36.1	--	
E _{on}	Turn-On Switching Loss		--	4.2	--	mJ
E _{off}	Turn-Off Switching Loss	--	1.47	--		
E _{ts}	Total Switching Loss	--	5.67	--		
t _{d(on)}	Turn-on Delay Time	V _{CE} =600V,I _C =40A, R _g =10Ω,V _{GE} =15V, Inductive Load, T _j =175℃	--	41	--	ns
t _r	Rise Time		--	43	--	
t _{d(off)}	Turn-Off Delay Time		--	292	--	
t _f	Fall Time		--	92	--	
E _{on}	Turn-On Switching Loss		--	4.44	--	mJ
E _{off}	Turn-Off Switching Loss	--	1.83	--		
E _{ts}	Total Switching Loss	--	6.27	--		
Q _g	Total Gate Charge	V _{CE} =600V,I _C =40A, V _{GE} =15V,	--	225	--	nC
Q _{ge}	Gate to Emitter Charge		--	23	--	
Q _{gc}	Gate to Collector Charge		--	130	--	
Electrical Characteristics of the DIODE						
V _F	Diode Forward Voltage	I _F =40A TC=25℃	--	2.4	3.2	V
		I _F =40A TC=175℃	--	1.85	--	V
t _{rr}	Reverse Recovery Time	I _F =40A di/dt=100A/μS	--	123	--	ns
I _{rrm}	Reverse Recovery Current		--	3.6	--	A
Q _{rr}	Reverse Recovery Charge		--	223	--	nC

Notes:

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: Overload condition, it is allowed to operate under the maximum junction temperature $T_{vjop} = 175^\circ C$, the maximum duty cycle is less than 20% (lasting for 60s at most)

Typical Performance Characteristics

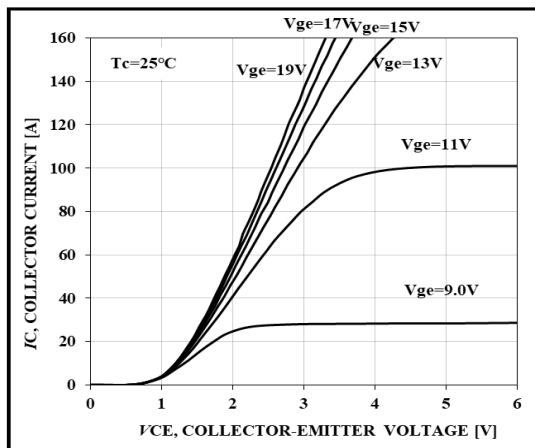


Figure 1. Output Characteristics

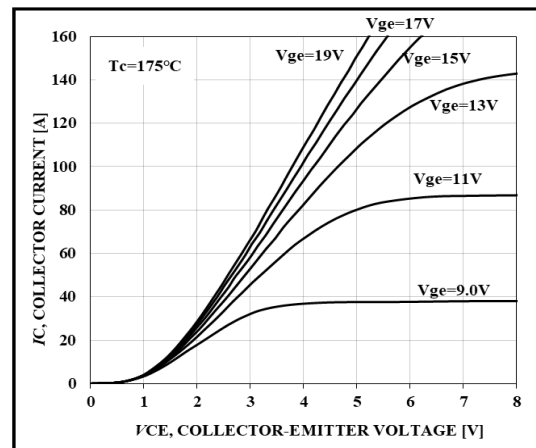


Figure 2. Output Characteristics

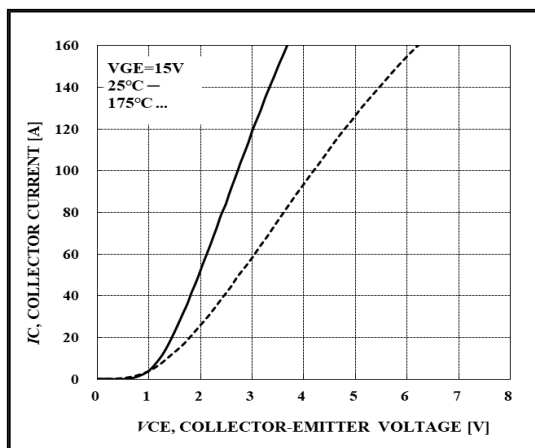


Figure 3. Saturation Voltage Characteristics

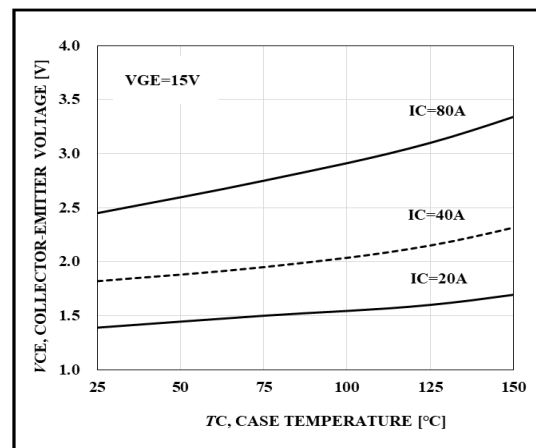


Figure 4. Saturation Voltage - T_c Characteristics

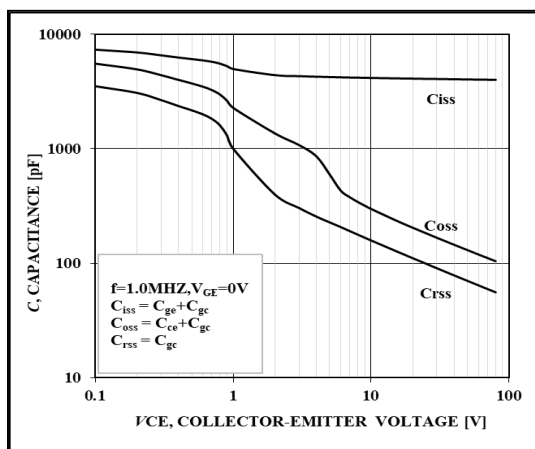


Figure 5. Capacitance Characteristics

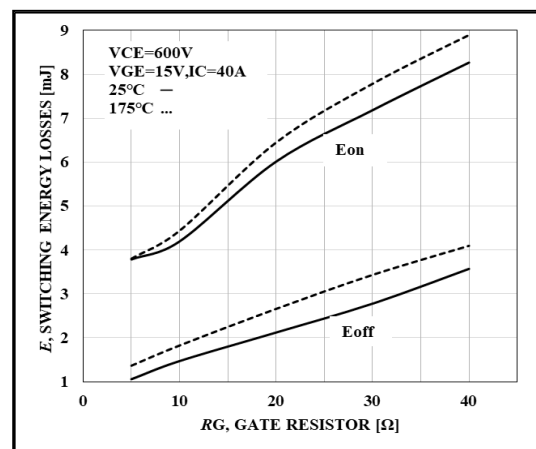


Figure 6. Switching Loss- R_G Characteristics

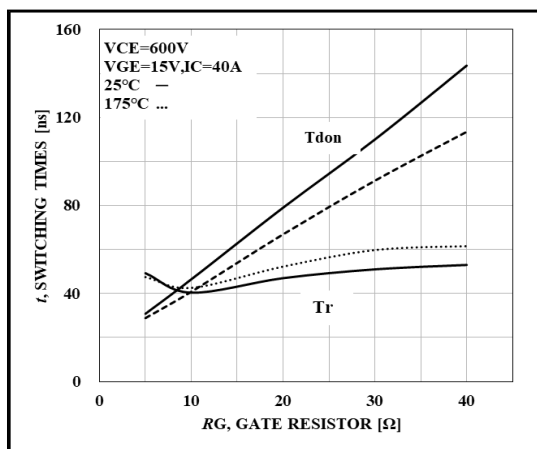


Figure 7. Switching Time- R_G Characteristics

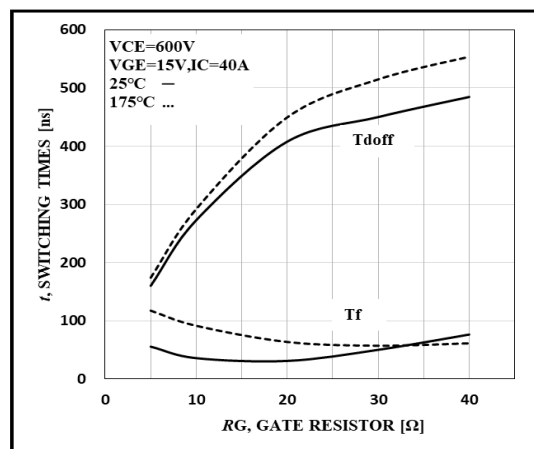


Figure 8. Switching Time- R_G Characteristics

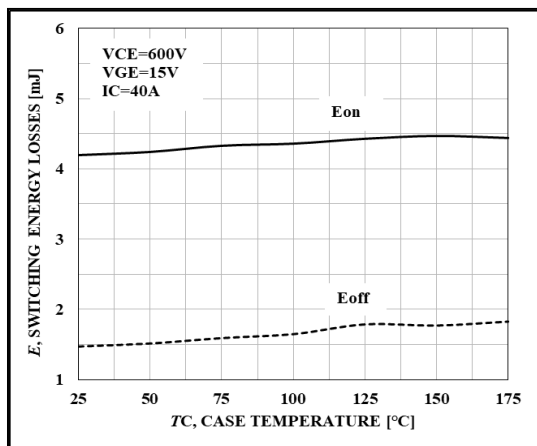


Figure 9. Switching Loss- T_c Characteristics

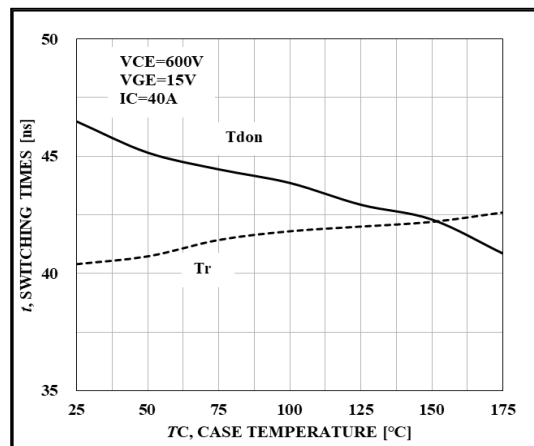


Figure 10. Switching Time- T_c Characteristics

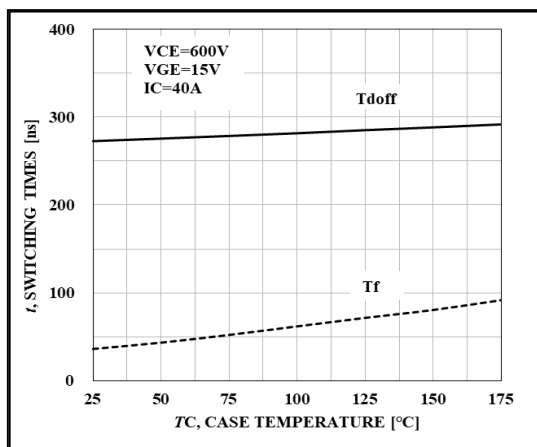


Figure 11. Switching Time- T_c Characteristics

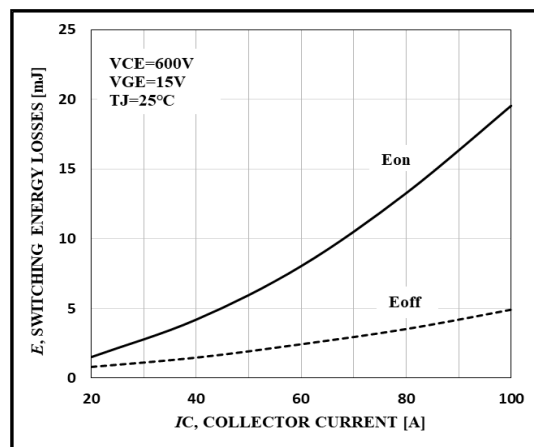


Figure 12. Switching Loss- I_C Characteristics

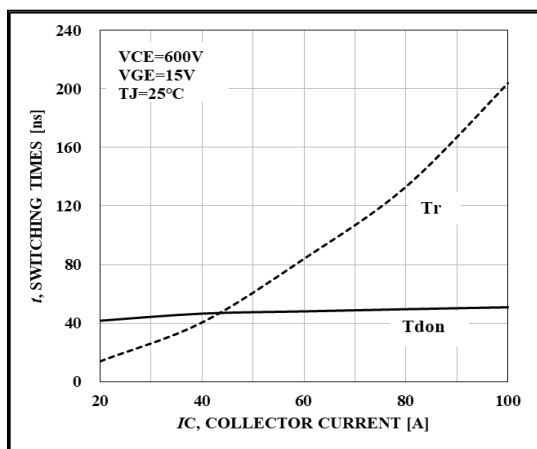


Figure 13. Switching Time- I_C Characteristics

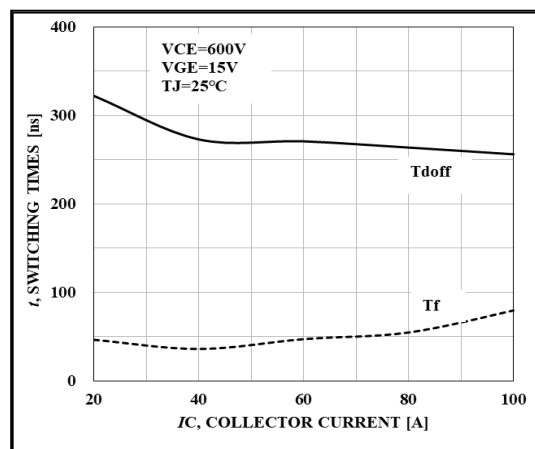


Figure 14. Switching Time- I_C Characteristics

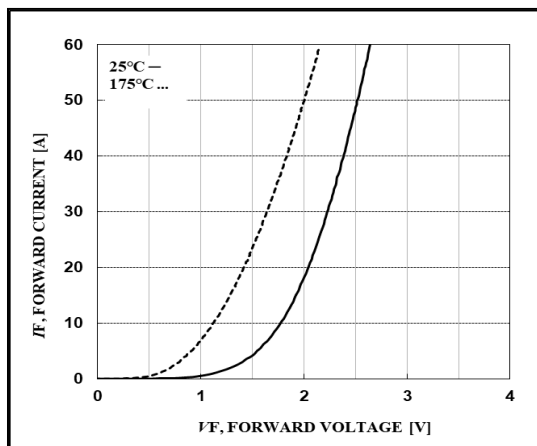


Figure 15. Diode Forward Characteristics

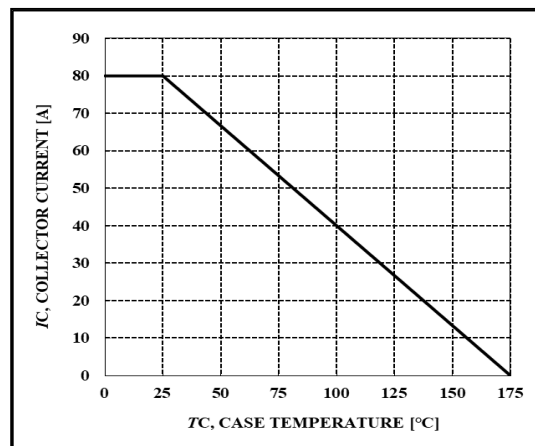


Figure 16. Collector Current- T_C Characteristics
($T_J \leq 175^\circ C$)

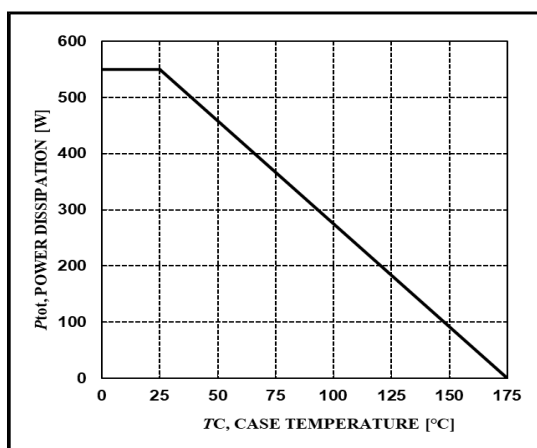


Figure 17. Power Dissipation- T_C Characteristics
($T_J \leq 175^\circ C$)

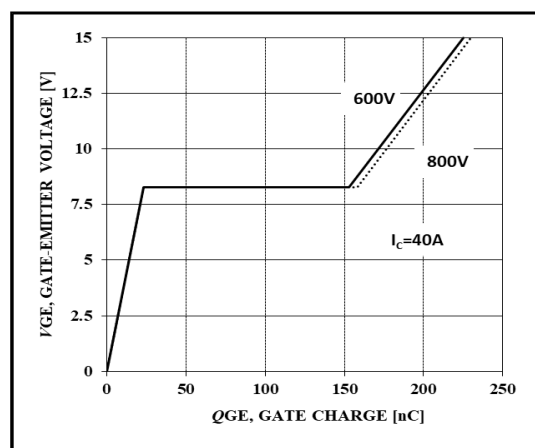


Figure 18. Gate Charge Characteristics

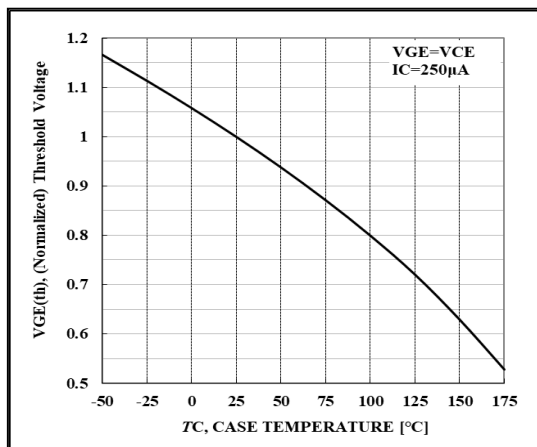


Figure 19. Threshold Voltage -Tc Characteristics

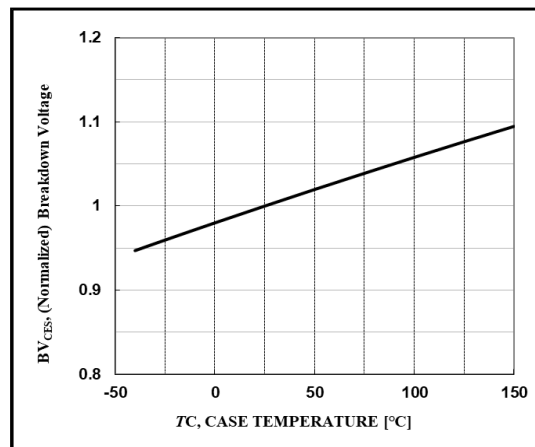


Figure 20. Breakdown Voltage-Tc Characteristics

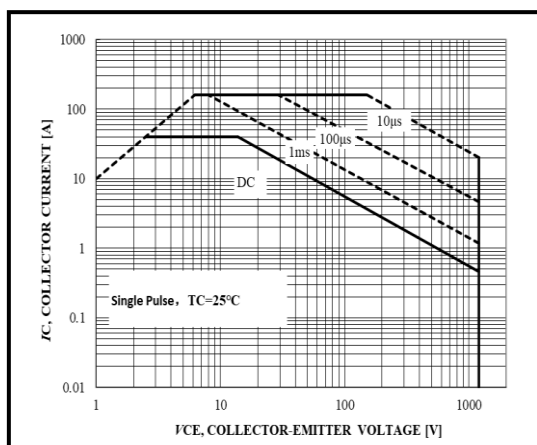


Figure 21. Forward Bias Safe Operating Area

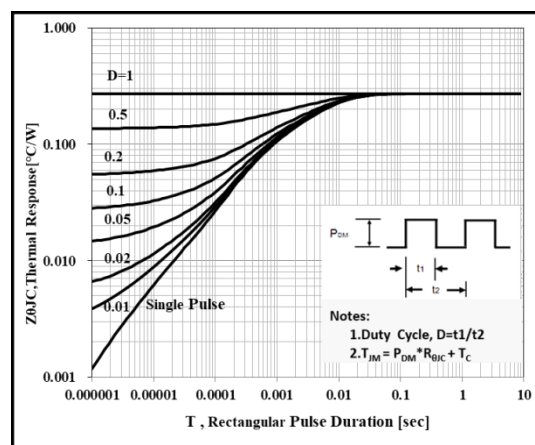
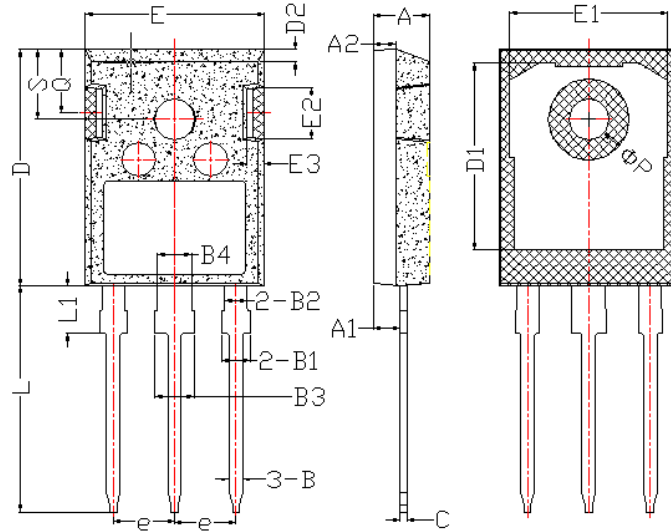


Figure 22. IGBT Transient Thermal Impedance

Package Information



Item	Value (mm)	
	MIN	MAX
A	4.6	5.2
A1	2.2	2.6
B	0.9	1.4
B1	1.75	2.35
B2	1.75	2.15
B3	2.8	3.35
B4	2.8	3.15
C	0.5	0.7
D	20.60	21.30
D1	16	18
E	15.5	16.10
E1	13	14.7
E2	3.80	5.3
E3	0.8	2.60
e	5.2	5.7
L	19	20.5
L1	3.9	4.6
ΦP	3.3	3.70
Q	5.2	6.00
S	5.8	6.6

TO-247 Package

**The name and content of poisonous and harmful material in products**

Part's Name Limit	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○: Means the hazardous material is under the criterion of 2011/65/EU. ×: Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.									

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